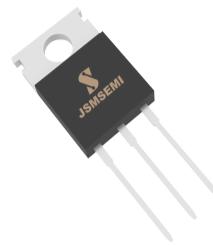
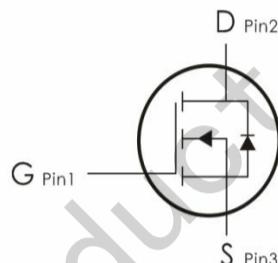


## FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



TO-220-3L



## Device Marking and Package Information

Device	Package	Marking
IRFB4020PBF	TO-220	IRFB4020

## Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , unless otherwise noted

Parameter	Symbol	Value	Unit
		TO-220	
Drain-Source Voltage ( $V_{GS} = 0\text{V}$ )	$V_{DSS}$	200	V
Continuous Drain Current	$I_D$	18	A
Pulsed Drain Current (note1)	$I_{DM}$	72	A
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Single Pulse Avalanche Energy (note2)	$E_{AS}$	262.7	mJ
Avalanche Current (note1)	$I_{AS}$	7.3	A
Repetitive Avalanche Energy (note1)	$E_{AR}$	157.62	mJ
Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_D$	104	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150	°C

## Thermal Resistance

Parameter	Symbol	Value	Unit
		TO-220	
Thermal Resistance, Junction-to-Case	$R_{thJC}$	1.2	K/W
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	60	

**Specifications  $T_J = 25^\circ\text{C}$ , unless otherwise noted**

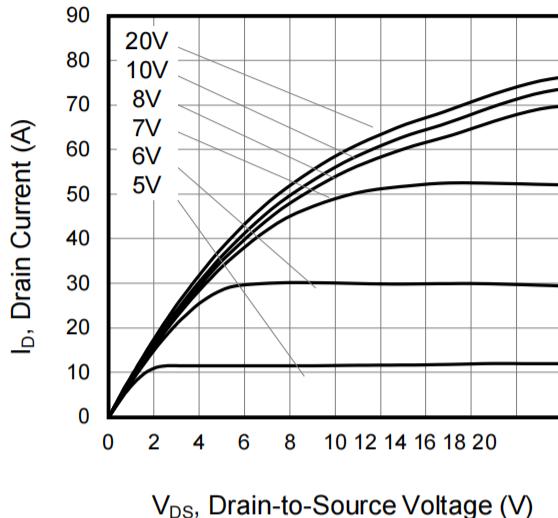
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	200	--	--	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}} = 200\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 25^\circ\text{C}$	--	--	1	$\mu\text{A}$
Gate-Source Leakage	$I_{\text{GSS}}$	$V_{\text{GS}} = \pm 20\text{V}$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	2.0	--	4.0	V
Drain-Source On-Resistance (Note3)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 9\text{A}$	--	0.10	0.11	$\Omega$
<b>Dynamic</b>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 25\text{V}, f = 1.0\text{MHz}$	--	1200	--	pF
Output Capacitance	$C_{\text{oss}}$		--	161	--	
Reverse Transfer Capacitance	$C_{\text{rss}}$		--	70	--	
Total Gate Charge	$Q_g$	$V_{\text{DD}} = 160\text{V}, I_D = 18\text{A}, V_{\text{GS}} = 10\text{V}$	--	38	--	nC
Gate-Source Charge	$Q_{\text{gs}}$		--	6	--	
Gate-Drain Charge	$Q_{\text{gd}}$		--	16	--	
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 100\text{V}, I_D = 18\text{A}, R_G = 25\Omega$	--	40	--	ns
Turn-on Rise Time	$t_r$		--	33	--	
Turn-off Delay Time	$t_{\text{d}(\text{off})}$		--	166	--	
Turn-off Fall Time	$t_f$		--	60	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	18	A
Pulsed Diode Forward Current	$I_{\text{SM}}$		--	--	72	
Body Diode Voltage	$V_{\text{SD}}$	$T_J = 25^\circ\text{C}, I_{\text{SD}} = 9\text{A}, V_{\text{GS}} = 0\text{V}$	--	--	1.4	V
Reverse Recovery Time	$t_{\text{rr}}$	$V_{\text{GS}} = 0\text{V}, I_S = 18\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	--	182	--	ns
Reverse Recovery Charge	$Q_{\text{rr}}$		--	1.29	--	$\mu\text{C}$

**Notes**

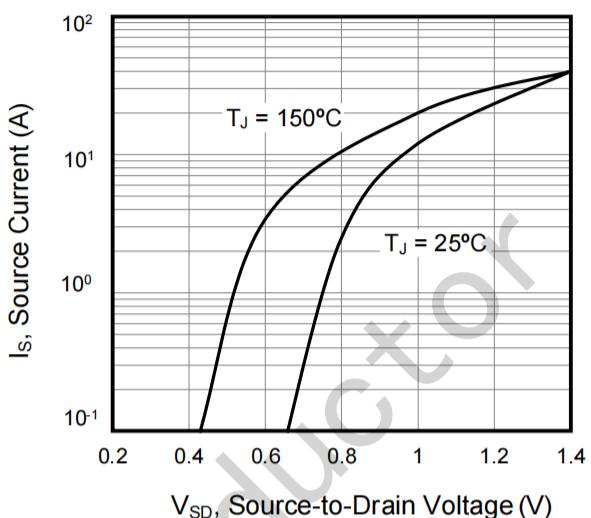
- Repetitive Rating: Pulse width limited by maximum junction temperature
- $I_{AS} = 15\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
- Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 1\%$

**Typical Characteristics**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

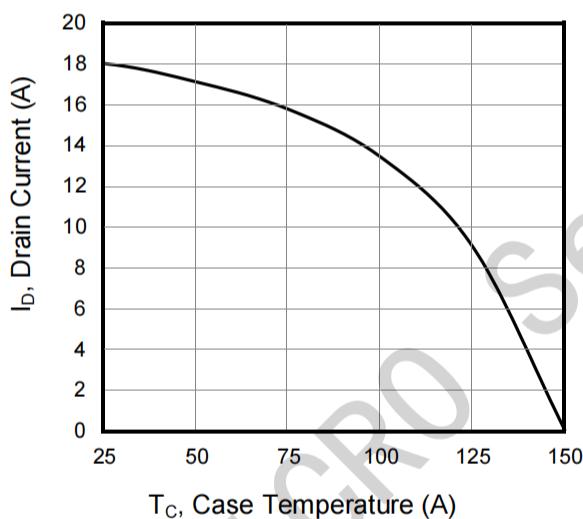
**Figure 1. Output Characteristics ( $T_J = 25^\circ\text{C}$ )**



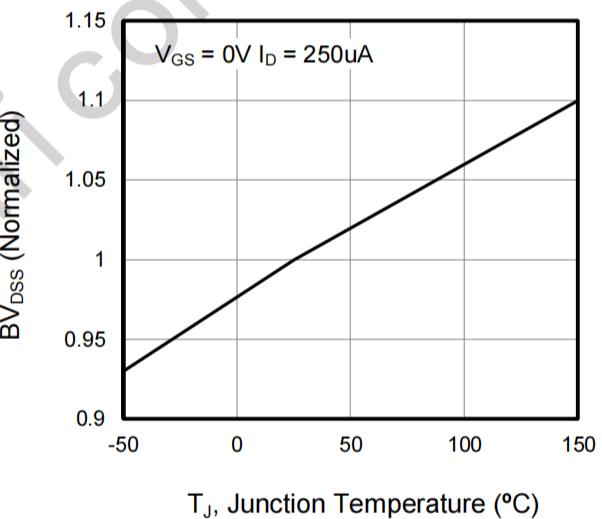
**Figure 2. Body Diode Forward Voltage**



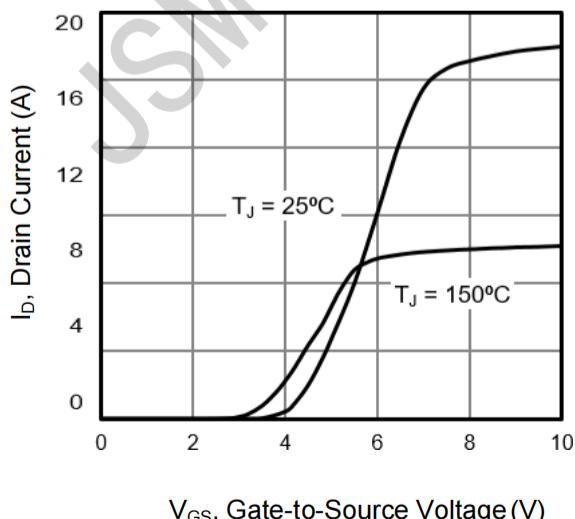
**Figure 3. Drain Current vs. Temperature**



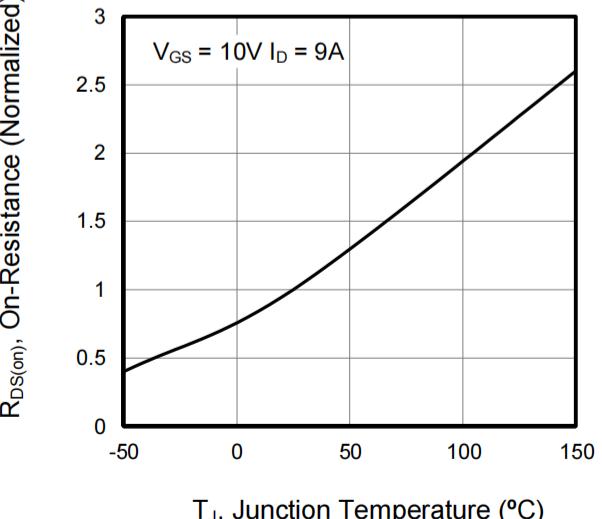
**Figure 4. BV<sub>DSS</sub> Variation vs. Temperature**



**Figure 5. Transfer Characteristics**

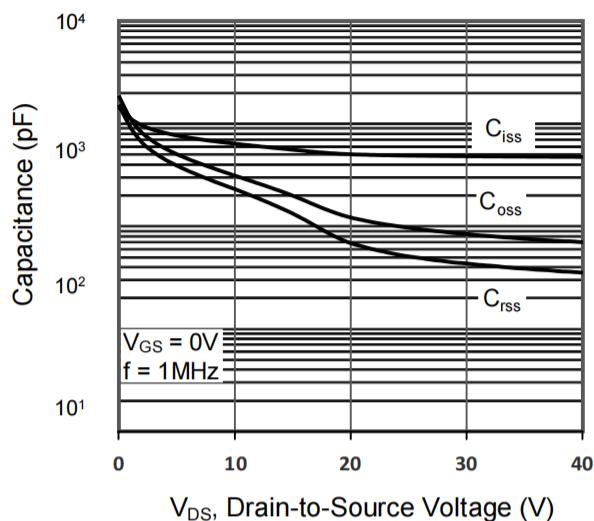


**Figure 6. On-Resistance vs. Temperature**

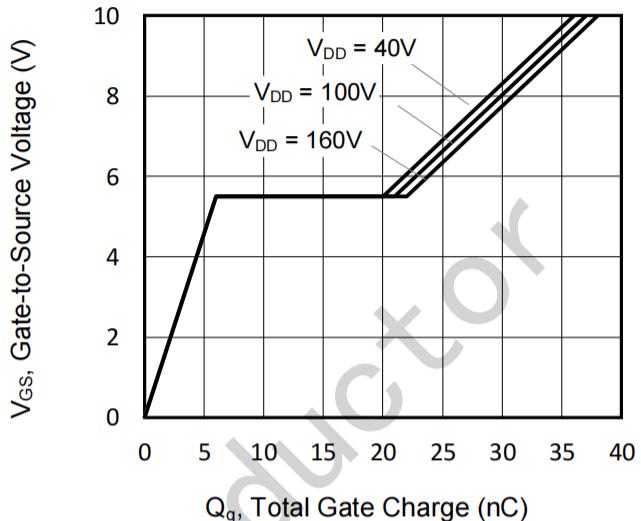


**Typical Characteristics**  $T_J = 25^\circ\text{C}$ , unless otherwise noted

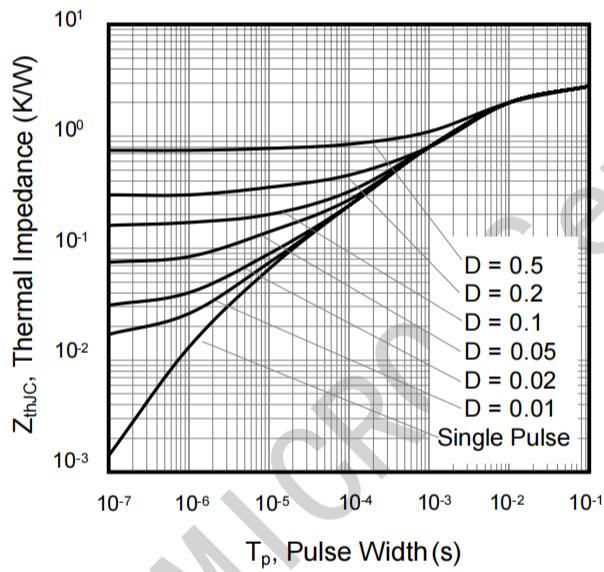
**Figure 7. Capacitance**



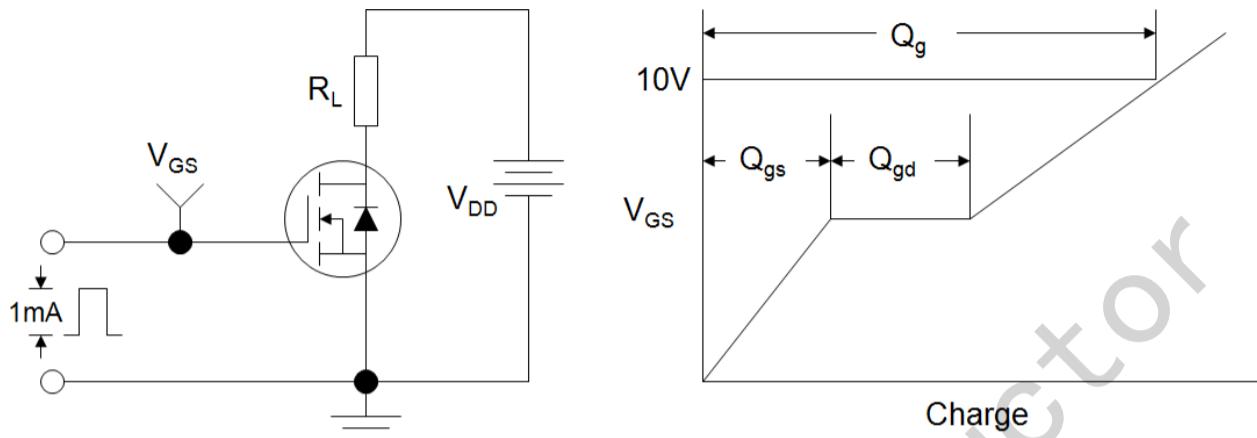
**Figure 8. Gate Charge**



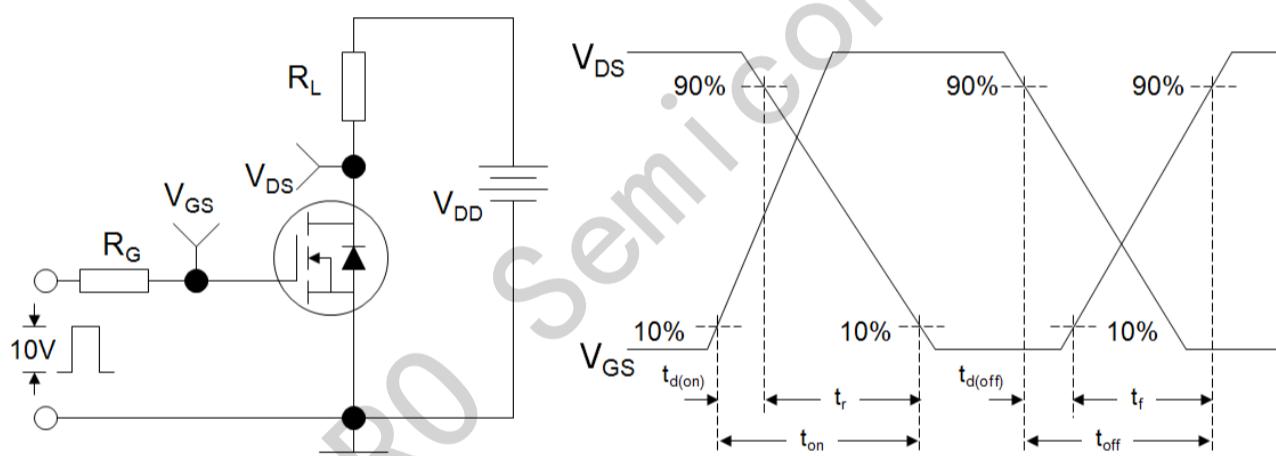
**Figure 9. Transient Thermal Impedance**



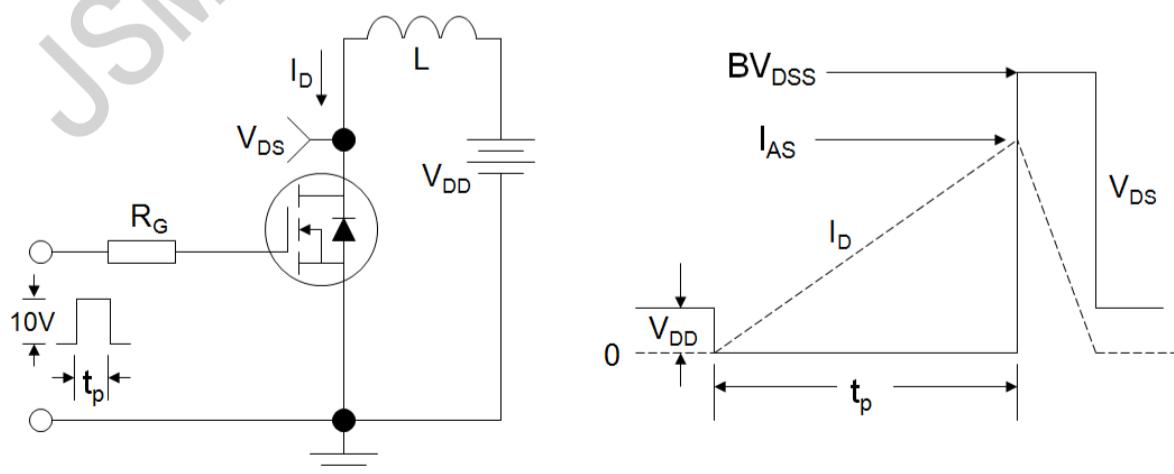
**Figure A: Gate Charge Test Circuit and Waveform**



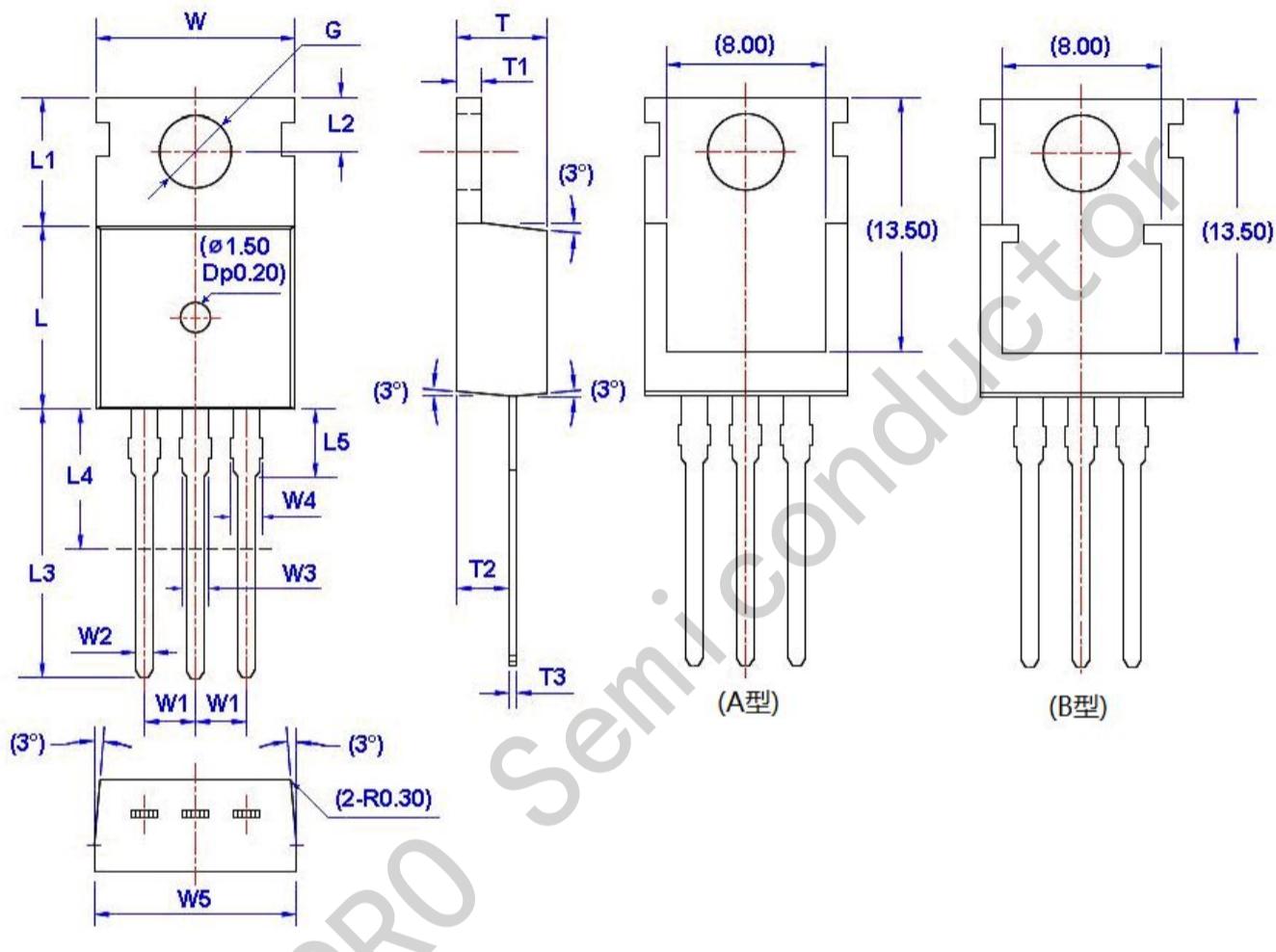
**Figure B: Resistive Switching Test Circuit and Waveform**



**Figure C: Unclamped Inductive Switching Test Circuit and Waveform**



## Package Outline: TO-220



Unit: mm

Symbol	Size		Symbol	Size		Symbol	Size		Symbol	Size	
	Min	Max		Min	Max		Min	Max		Min	Max
W	9.66	10.28	W5	9.80	10.20	L4**	6.20	6.60	T3	0.45	0.60
W1	2.54 (TYP)		L	9.00	9.40	L5	2.79	3.30	G(Φ)	3.50	3.70
W2	0.70	0.95	L1	6.40	6.80	T	4.30	4.70			
W3	1.17	1.37	L2	2.70	2.90	T1	1.15	1.40			
W4*	1.32	1.72	L3	12.70	14.27	T2	2.20	2.60			